HFZT

MMBD914

Small Signal Switching Diodes

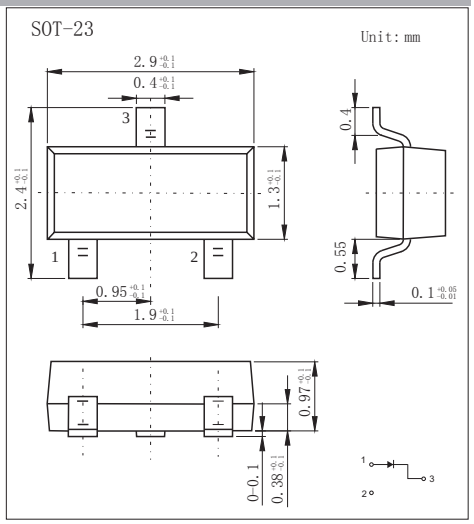
VOLTAGE RANGE: 100V
PEAK PULSE POWER:350mW

FEATURES

- High-Speed Switching Diode

MECHANICAL DATA

- Case: SOT-23 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Output Current	I_O	300	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

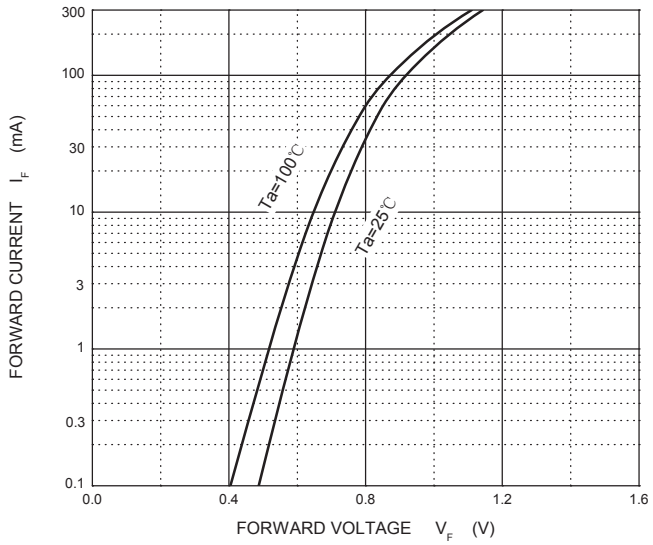
Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	100			V	I_R=100μA
Forward Voltage	V_{F1}			715	mV	I_F=1mA
	V_{F2}			855	mV	I_F=10mA
	V_{F3}			1000	mV	I_F=50mA
	V_{F4}			1250	mV	I_F=150mA
Reverse Current	I_{R1}			1	uA	V_R=75V
	I_{R2}			25	nA	V_R=20V
Diode Capacitance	C_D			2	pF	V_R=0,f=1MHz
Reverse Recovery Time	t_{rr}			4	ns	I_F =I_R=10mA, I_{rr}=0.1*I_R

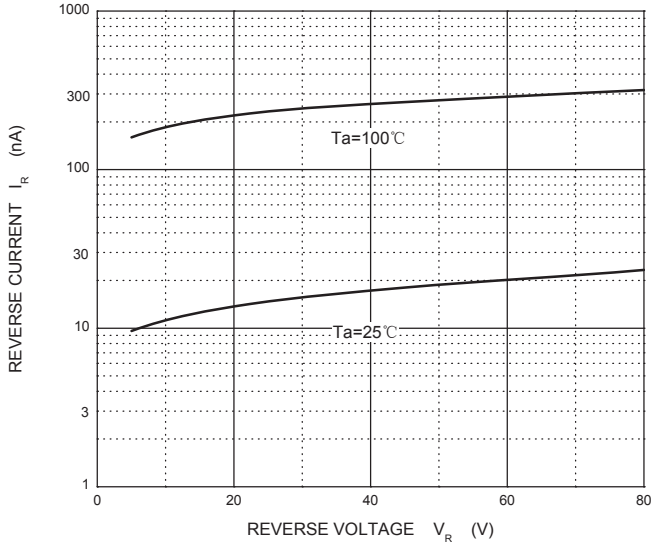
MARKING: 5D

RATINGS AND CHARACTERISTIC CURVES

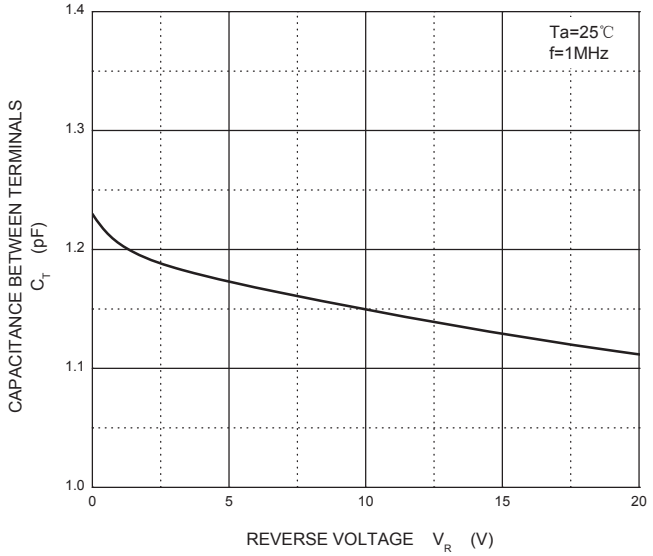
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve